Pb Free Product

NCE N-Channel Enhancement Mode Power MOSFET

Description

The NCE3008M uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other switching application.

General Feature

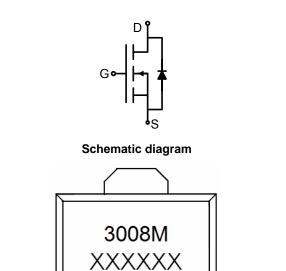
V_{DS} =30V,I_D =8A

$$\begin{split} R_{DS(ON)} <& 22.5 m\Omega \text{ @ V}_{GS} =& 10 V \\ R_{DS(ON)} <& 32 m\Omega \text{ @ V}_{GS} =& 4.5 V \end{split}$$

- High Power and current handing capability
- Lead free product is acquired
- Surface mount package

Application

- Battery switch
- ●DC/DC converter



SOT-89 -3L top view

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
3008M	NCE3008M	SOT-89-3L	Ø180mm	12mm	1000units

Absolute Maximum Ratings (T_A=25 ℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	30	V
Gate-Source Voltage	V _G S	±20	V
Drain Current-Continuous	I _D	8	Α
Drain Current-Pulsed (Note 1)	I _{DM}	30	А
Maximum Power Dissipation	P _D	3.5	W
Operating Junction and Storage Temperature Range	T_{J}, T_{STG}	-55 To 150	$^{\circ}$

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	35	°C/W

Electrical Characteristics (T_A=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	30	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =30V,V _{GS} =0V	-	-	1	μA



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Parameter	Symbol	Condition	Min	Тур	Max	Unit
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$, $I_{D}=250\mu A$	1.0	1.6	2.4	V
Drain-Source On-State Resistance	В	V _{GS} =10V, I _D =8A	-	19.8	22.5	mΩ
Diain-Source Oil-State Resistance	R _{DS(ON)}	V_{GS} =4.5V, I_D =6A	-	27	31	mΩ
Dynamic Characteristics (Note4)	•		•			
Input Capacitance	C _{lss}	\/ -15\/\/ -0\/	-	564	-	PF
Output Capacitance	Coss	V _{DS} =15V,V _{GS} =0V, F=1.0MHz	-	75	-	PF
Reverse Transfer Capacitance	C _{rss}	r-1.0ivinz	-	66	-	PF
Switching Characteristics (Note 4)	•		•			
Turn-on Delay Time	t _{d(on)}		-	9	-	nS
Turn-on Rise Time	t _r	V_{DD} =30 V , I_{D} =1.5 A	-	10	-	nS
Turn-Off Delay Time	t _{d(off)}	V_{GS} =10 V , R_{GEN} =1 Ω	-	15	-	nS
Turn-Off Fall Time	t _f		-	5	-	nS
Total Gate Charge	Q _g	\/ -20\/ -0.4	-	14.2	-	nC
Gate-Source Charge	Q _{gs}	V_{DS} =30V, I_{D} =8A, V_{GS} =10V	-	1.5	-	nC
Gate-Drain Charge	Q_{gd}	VGS-10V	-	3.6	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =8A	-	-	1.2	V
Diode Forward Current (Note 2)	Is		-	-	8	Α

Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, t ≤ 10 sec.
- 3. Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2%.
- 4. Guaranteed by design, not subject to production



Typical Electrical and Thermal Characteristics

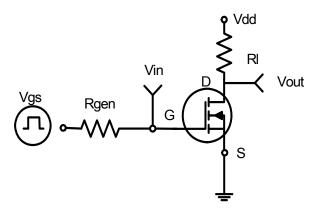


Figure 1 Switching Test Circuit

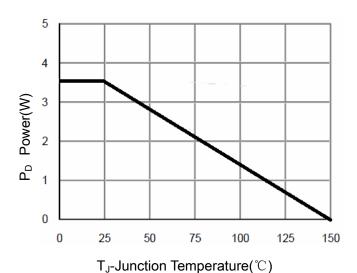


Figure 3 Power Dissipation

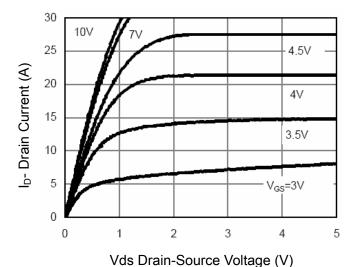


Figure 5 Output Characteristics

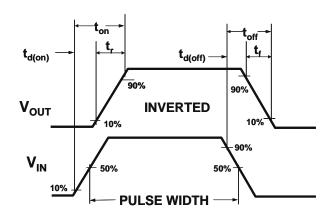


Figure 2 Switching Waveforms

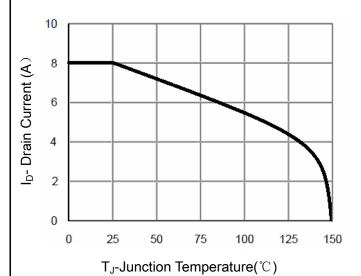


Figure 4 Drain Current

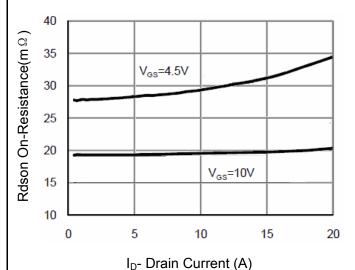


Figure 6 Drain-Source On-Resistance



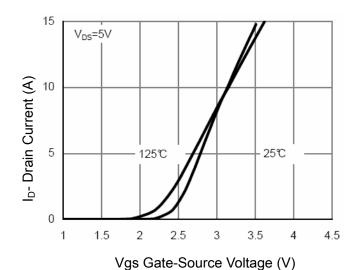
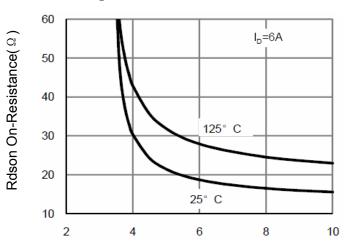


Figure 7 Transfer Characteristics



Vgs Gate-Source Voltage (V)
Figure 9 Rdson vs Vgs

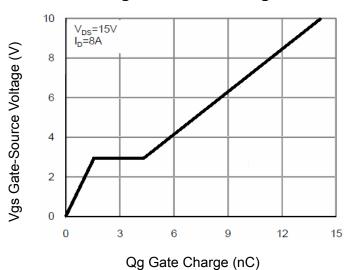


Figure 11 Gate Charge

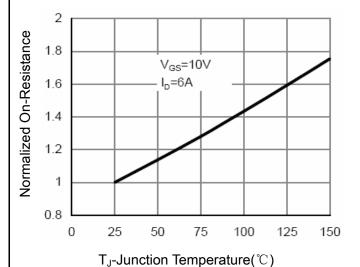
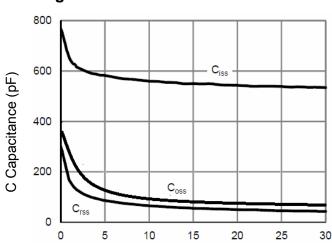


Figure 8 Drain-Source On-Resistance



Vds Drain-Source Voltage (V)

Figure 10 Capacitance vs Vds

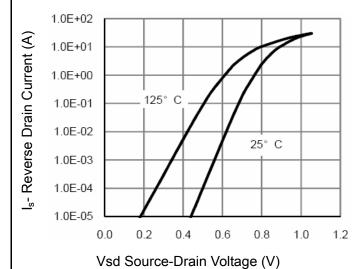
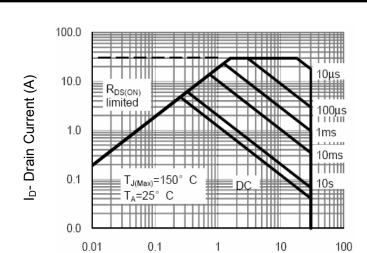


Figure 12 Source- Drain Diode Forward



Vds Drain-Source Voltage (V)

Figure 13 Safe Operation Area

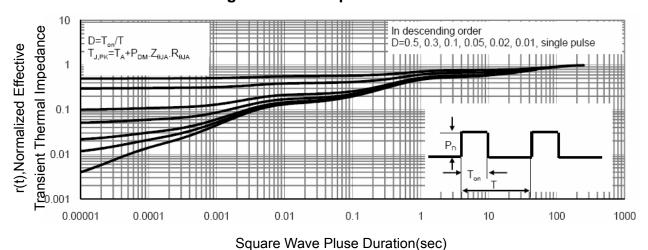
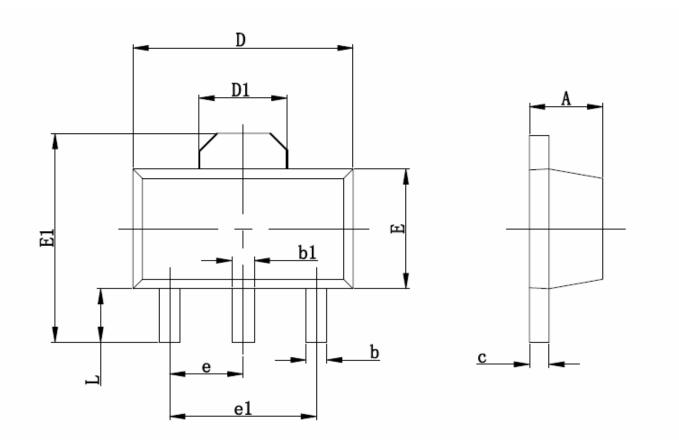


Figure 14 Normalized Maximum Transient Thermal Impedance



NCE3008M

SOT-89-3L Package Information



Symbol	Dimensions	In Millimeters	Dimensions In Inches		
	Min	Max	Min	Max	
Α	1.400	1.600	0.055	0.063	
b	0.350	0.520	0.013	0.197	
b1	0.400	0.580	0.016	0.023	
С	0.350	0.440	0.014	0.017	
D	4.400	4.600	0.173	0.181	
D1	1.550 REF		0.061 REF		
E	2.350	2.550	0.091	0.102	
E1	3.940	4.250	0.155	0.167	
е	1.500) TYP	0.060TYP		
e1	3.000 TYP		0.118TYP		
L	0.900	1.100	0.035	0.047	



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